



## NTR0202PLT3G Information



For Reference Only

Part Number NTR0202PLT3G
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH 20V 400MA SOT-23

**Package** TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# NTR0202PLT3G Specifications

Manufacturer Part Number         NTR0202PLT3G           Manufacturer         ON Semiconductor           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-236-3, SC-59, SOT-23-3           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         20V           Current - Continuous Drain (Id) @ 25°C         400mA (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.3V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         2.18nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         70pF @ 5V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         225mW (Ta)           Rds On (Max) @ Id, Vgs         800 mOhm @ 200mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-23-3 (TO-236)           Package / Case         TO-236-3, SC-59, SOT-23-3           Report errors?		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-236-3, SC-59, SOT-23-3           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         20V           Current - Continuous Drain (Id) @ 25°C         400mA (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.3V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         2.18nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         70pF @ 5V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         225mW (Ta)           Rds On (Max) @ Id, Vgs         800 mOhm @ 200mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-23-3 (TO-236)           Package / Case         TO-236-3, SC-59, SOT-23-3	Manufacturer Part Number	NTR0202PLT3G
Package         TCO-236-3, SC-59, SOT-23-3           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         20V           Current - Continuous Drain (Id) @ 25°C         400mA (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.3V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         2.18nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         70pF @ 5V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         225mW (Ta)           Rds On (Max) @ Id, Vgs         800 mOhm @ 200mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-23-3 (TO-236)           Package / Case         TO-236-3, SC-59, SOT-23-3	Manufacturer	ON Semiconductor
Package         TO-236-3, SC-59, SOT-23-3           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         20V           Current - Continuous Drain (Id) @ 25°C         400mA (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.3V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         2.18nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         70pF @ 5V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         225mW (Ta)           Rds On (Max) @ Id, Vgs         800 mOhm @ 200mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-23-3 (TO-236)           Package / Case         TO-236-3, SC-59, SOT-23-3	Category	Discrete Semiconductor Products
Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         20V           Current - Continuous Drain (Id) @ 25°C         400mA (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.3V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         2.18nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         70pF @ 5V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         225mW (Ta)           Rds On (Max) @ Id, Vgs         800 mOhm @ 200mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-23-3 (TO-236)           Package / Case         TO-236-3, SC-59, SOT-23-3		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 400mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 2.18nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 70pF @ 5V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 225mW (Ta) Rds On (Max) @ Id, Vgs 800 mOhm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case Took Continue (Table Device Package (Max) 200mA) (Max) 200mA, 10V TO-236-3, SC-59, SOT-23-3	Package	TO-236-3, SC-59, SOT-23-3
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  400mA (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Nogenating Temperature  Poperating Temperature  Supplier Device Package  Package / Case  MOSFET (Metal Oxide)  20V  400mA (Ta)  4.5V, 10V  2.3V @ 250µA  2.18nC @ 10V  70pF @ 5V  2250W  TopF @ 5V  220V  FET Feature  Supplier Device Package  SOT-23-3 (TO-236)  TO-236-3, SC-59, SOT-23-3	Series	-
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C400mA (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs2.18nC @ 10VInput Capacitance (Ciss) (Max) @ Vds70pF @ 5VVgs (Max)±20VFET Feature-Power Dissipation (Max)225mW (Ta)Rds On (Max) @ Id, Vgs800 mOhm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C 400mA (Ta)  Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V  Vgs(th) (Max) @ Id 2.3V @ 250µA  Gate Charge (Qg) (Max) @ Vgs 2.18nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds 70pF @ 5V  Vgs (Max) ±20V  FET Feature -  Power Dissipation (Max) 225mW (Ta)  Rds On (Max) @ Id, Vgs 800 mOhm @ 200mA, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Surface Mount  Supplier Device Package SOT-23-3 (TO-236)  Package / Case TO-236-3, SC-59, SOT-23-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs2.18nC @ 10VInput Capacitance (Ciss) (Max) @ Vds70pF @ 5VVgs (Max)±20VFET Feature-Power Dissipation (Max)225mW (Ta)Rds On (Max) @ Id, Vgs800 mOhm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id       2.3V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       2.18nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       70pF @ 5V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       225mW (Ta)         Rds On (Max) @ Id, Vgs       800 mOhm @ 200mA, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       SOT-23-3 (TO-236)         Package / Case       TO-236-3, SC-59, SOT-23-3	Current - Continuous Drain (Id) @ 25°C	400mA (Ta)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  70pF @ 5V  Vgs (Max)  ±20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  800 mOhm @ 200mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  TO-236-3, SC-59, SOT-23-3	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Power Disarrature  Surface Mount  Supplier Device Package  Package / Case  TO-236-3, SC-59, SOT-23-3	Vgs(th) (Max) @ Id	2.3V @ 250μA
Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       225mW (Ta)         Rds On (Max) @ Id, Vgs       800 mOhm @ 200mA, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       SOT-23-3 (TO-236)         Package / Case       TO-236-3, SC-59, SOT-23-3	Gate Charge (Qg) (Max) @ Vgs	2.18nC @ 10V
FET Feature -  Power Dissipation (Max) 225mW (Ta)  Rds On (Max) @ Id, Vgs 800 mOhm @ 200mA, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Surface Mount  Supplier Device Package SOT-23-3 (TO-236)  Package / Case TO-236-3, SC-59, SOT-23-3	Input Capacitance (Ciss) (Max) @ Vds	70pF @ 5V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  800 mOhm @ 200mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  SOT-23-3 (TO-236)  Package / Case  TO-236-3, SC-59, SOT-23-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs800 mOhm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  SOT-23-3 (TO-236)  Package / Case  TO-236-3, SC-59, SOT-23-3	Power Dissipation (Max)	225mW (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Rds On (Max) @ Id, Vgs	800 mOhm @ 200mA, 10V
Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-236-3, SC-59, SOT-23-3	Mounting Type	Surface Mount
	Supplier Device Package	SOT-23-3 (TO-236)
Report errors?	Package / Case	TO-236-3, SC-59, SOT-23-3
		Report errors?

#### NTR0202PLT3G Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# NTR0202PLT3G Payment Methods



















### NTR0202PLT3G Shipping Methods













If you have any question about NTR0202PLT3G, please do not hesitate to contact us!

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